TOSHIBA Field Effect Transistor Silicon N Channel MOS Type ( $\pi$ -MOSVI)

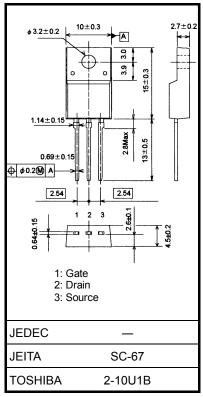
# 2SK3767

#### Switching Regulator Applications

- Low drain-source ON resistance: R<sub>DS</sub> (ON) = 3.3 Ω (typ.)
- High forward transfer admittance: |Y<sub>fs</sub>| = 1.6 S (typ.)
- Low leakage current: I<sub>DSS</sub> = 100 μA (V<sub>DS</sub> = 600 V)
- Enhancement mode:  $V_{th}$  = 2.0 to 4.0 V ( $V_{DS}$  = 10 V,  $I_D$  = 1 mA)

#### Characteristics Symbol Rating Unit Drain-source voltage VDSS 600 ٧ 600 V Drain-gate voltage ( $R_{GS} = 20 \text{ k}\Omega$ ) VDGR V Gate-source voltage ±30 VGSS DC 2 (Note 1) $I_D$ Drain current A Pulse (Note 1) IDP 5 Drain power dissipation ( $Tc = 25^{\circ}C$ ) $\mathsf{P}_\mathsf{D}$ 25 w Single pulse avalanche energy EAS 93 mJ (Note 2) Avalanche current 2 А I<sub>AR</sub> Repetitive avalanche energy (Note 3) 4 EAR mJ Channel temperature 150 °C T<sub>ch</sub> Storage temperature range -55~150 °C Tstq

#### Absolute Maximum Ratings (Ta = 25°C)



Weight : 1.7 g (typ.)

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

#### **Thermal Characteristics**

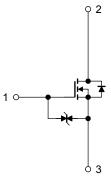
Characteristics	Symbol	Max	Unit	
Thermal resistance, channel to case	R <sub>th (ch-c)</sub>	5.0	°C/W	
Thermal resistance, channel to ambient	R <sub>th (ch-a)</sub>	62.5	°C/W	

Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2:  $V_{DD} = 90 \text{ V}, \text{ T}_{ch} = 25^{\circ}\text{C}$  (initial), L = 41mH, R<sub>G</sub> = 25  $\Omega$  , I<sub>AR</sub> = 2 A

Note 3: Repetitive rating: pulse width limited by maximum channel temperature

This transistor is an electrostatic-sensitive device. Please handle with caution.



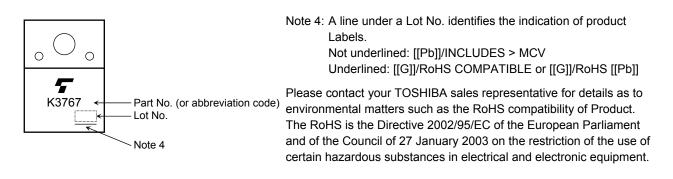
**Electrical Characteristics (Ta = 25°C)** 

Charae	cteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage curr	ent	I <sub>GSS</sub>	$V_{GS}=\pm 25~V,~V_{DS}=0~V$	_		±10	μA
Gate-source break	down voltage	V (BR) GSS	$I_G=\pm 10~\mu A,~V_{DS}=0~V$	±30			V
Drain cut-off curre	nt	I <sub>DSS</sub>	$V_{DS} = 600 \text{ V}, \text{ V}_{GS} = 0 \text{ V}$	_		100	μA
Drain-source brea	kdown voltage	V (BR) DSS	$I_D = 10 \text{ mA}, V_{GS} = 0 \text{ V}$	600			V
Gate threshold vol	tage	V <sub>th</sub>	$V_{DS} = 10 \text{ V}, \text{ I}_{D} = 1 \text{ mA}$	2.0		4.0	V
Drain-source ON r	esistance	R <sub>DS (ON)</sub>	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 1 A	_	3.3	4.5	Ω
Forward transfer a	dmittance	Y <sub>fs</sub>	$V_{DS} = 10 \text{ V}, \text{ I}_{D} = 1 \text{ A}$	0.8	1.6		S
Input capacitance		C <sub>iss</sub>		_	320		
Reverse transfer capacitance		C <sub>rss</sub>	$V_{DS}$ = 10 V, $V_{GS}$ = 0 V, f = 1 MHz	_	30		pF
Output capacitance		C <sub>oss</sub>			100		
Switching time	Rise time	tr	$10 V$ $V_{GS}$ $0 V$ $C_{GS}$ $C_{GS}$ $R_{L} =$ $200 \Omega$		15	_	ns
	Turn-on time	t <sub>on</sub>			55	—	
	Fall time	t <sub>f</sub>			20	—	
	Turn-off time	t <sub>off</sub>	$V_{DD}^{\cup} \simeq 200 \text{ V}$ Duty ≤ 1%, t <sub>w</sub> = 10 µs	_	80	_	
Total gate charge C		Qg		_	9		
Gate-source charge		Q <sub>gs</sub>	$V_{DD} \simeq 400 \text{ V}, \text{ V}_{GS} = 10 \text{ V}, \text{ I}_{D} = 2 \text{ A}$		5		nC
Gate-drain charge		Q <sub>gd</sub>		_	4	—	

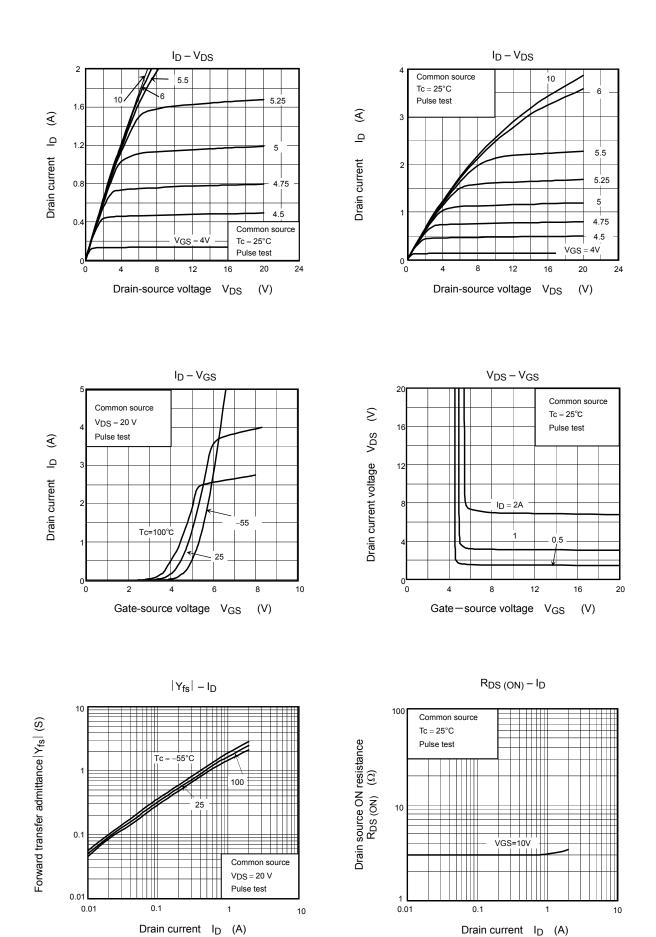
#### Source-Drain Ratings and Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Continuous drain reverse current (Note 1)	I <sub>DR</sub>	—	_	_	2	А
Pulse drain reverse current (Note 1)	I <sub>DRP</sub>	—	_	_	5	А
Forward voltage (diode)	V <sub>DSF</sub>	$I_{DR} = 2 \text{ A}, \text{ V}_{GS} = 0 \text{ V}$	_	_	-1.7	V
Reverse recovery time	t <sub>rr</sub>	$I_{DR}=2~\text{A},~\text{V}_{GS}=0~\text{V},$	_	1000	_	ns
Reverse recovery charge	Q <sub>rr</sub>	dl <sub>DR</sub> /dt = 100 A/μs	_	3.5	_	μC

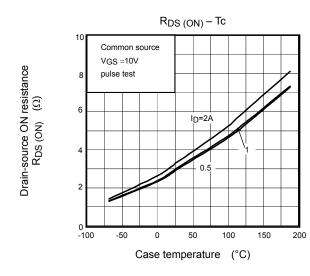
### Marking

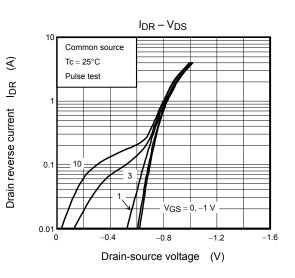


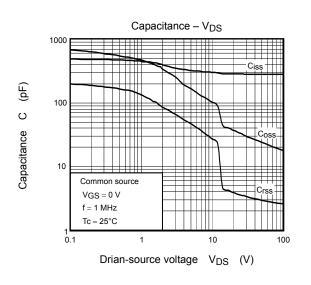
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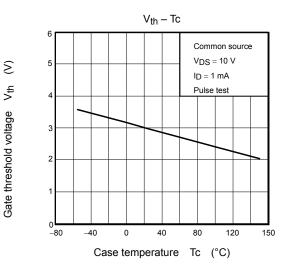
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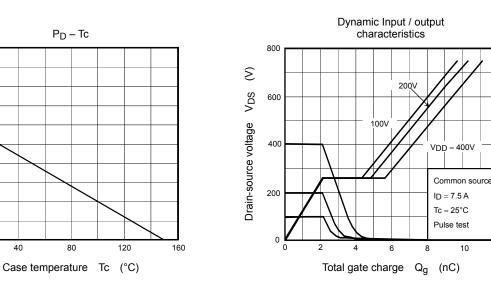


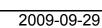




P<sub>D</sub> – Tc





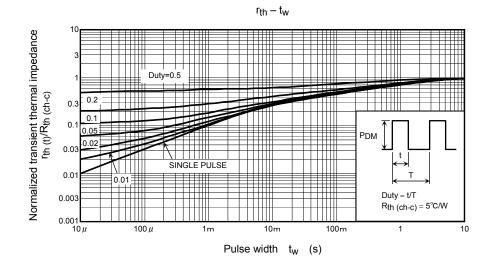


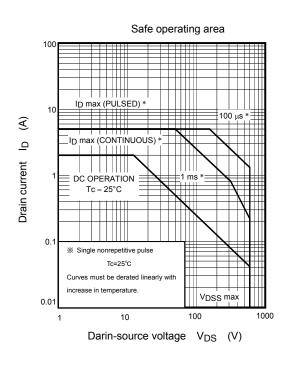
S

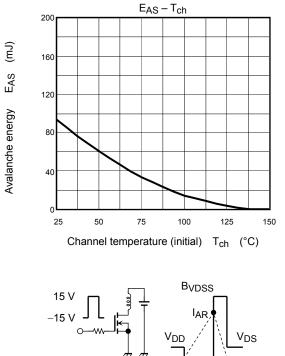
V<sub>GS</sub> 

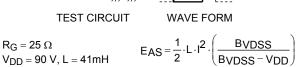
Gate-source voltage











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